

# FDC637AN

## Single N-Channel, 2.5V Specified PowerTrench™ MOSFET

### General Description

This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

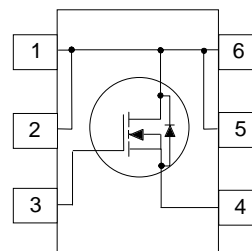
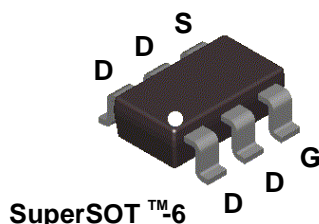
These devices have been designed to offer exceptional power dissipation in a very small footprint compared with bigger SO-8 and TSSOP-8 packages.

### Applications

- DC/DC converter
- Load switch
- Battery Protection

### Features

- 6.2 A, 20 V.  $R_{DS(on)} = 0.024 \Omega @ V_{GS} = 4.5 V$   
 $R_{DS(on)} = 0.032 \Omega @ V_{GS} = 2.5 V$
- Fast switching speed.
- Low gate charge (10.5nC typical).
- High performance trench technology for extremely low  $R_{DS(on)}$ .
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDC637AN	Units
V <sub>DSS</sub>	Drain-Source Voltage	20	V
V <sub>GSS</sub>	Gate-Source Voltage	±8	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a)	6.2	A
	Drain Current - Pulsed	20	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.6	W
		0.8	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	30	°C/W

### Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.637	FDC637AN	7"	8mm	3000 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		14		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

## On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.4	0.82	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $125^\circ\text{C}$		-3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 2.5\text{ V}, I_D = 5.2\text{ A}$		0.019 0.028 0.025	0.024 0.041 0.032	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	10			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 6.2\text{ A}$		7.4		S

## Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1125		pF
$C_{oss}$	Output Capacitance			290		pF
$C_{riss}$	Reverse Transfer Capacitance			145		pF

## Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		9	18	ns
$t_r$	Turn-On Rise Time			13	24	ns
$t_{d(off)}$	Turn-Off Delay Time			26	42	ns
$t_f$	Turn-Off Fall Time			11	20	ns
$Q_g$	Total Gate Charge	$V_{DS} = 5\text{ V}, I_D = 6.2\text{ A},$ $V_{GS} = 4.5\text{ V}$		10.5	16	nC
$Q_{gs}$	Gate-Source Charge			1.5		nC
$Q_{gd}$	Gate-Drain Charge			2.2		nC

## Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current			1.3		A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$ (Note 2)		0.7	1.2	V

### Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.
  - $78^\circ\text{C/W}$  when mounted on a  $1.0\text{ in}^2$  pad of 2 oz. copper.
  - $156^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz. copper.
- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

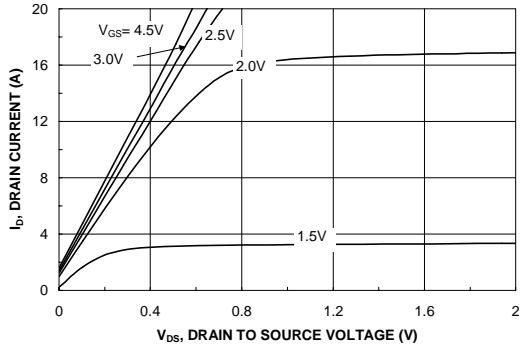


Figure 1. On-Region Characteristics.

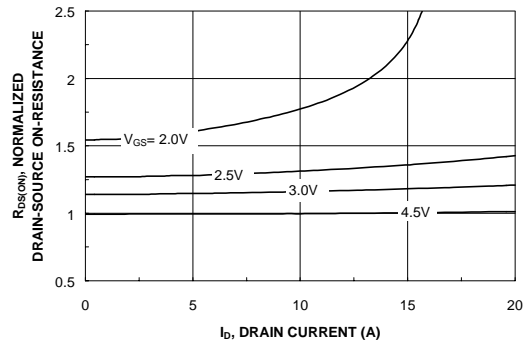


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

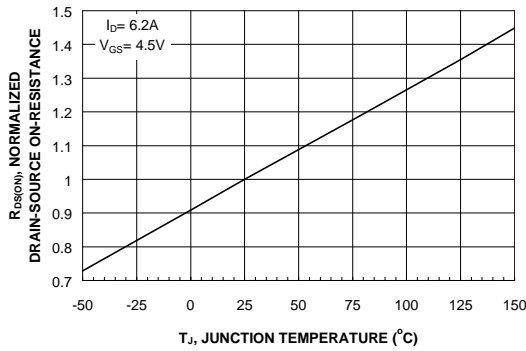


Figure 3. On-Resistance Variation with Temperature.

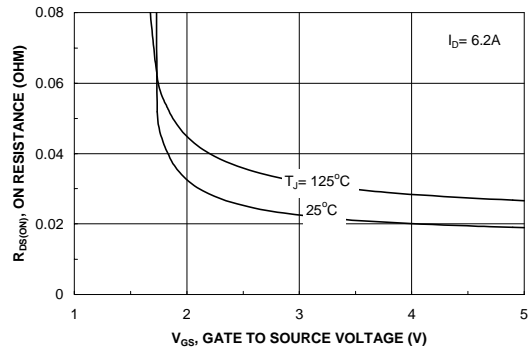


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

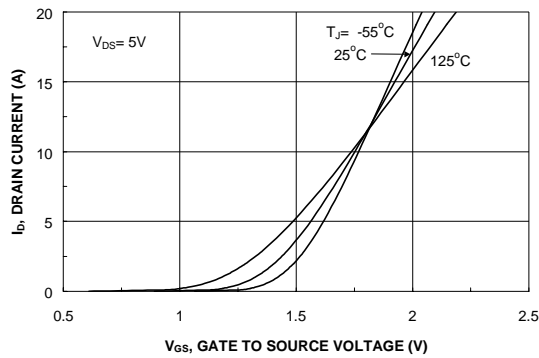


Figure 5. Transfer Characteristics.

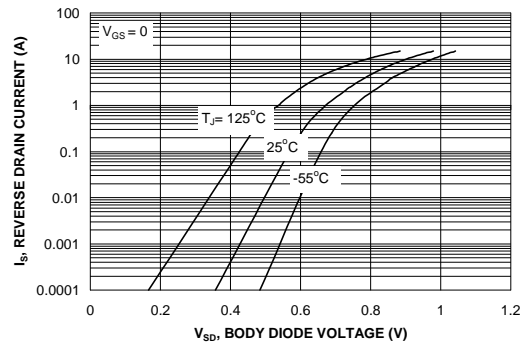
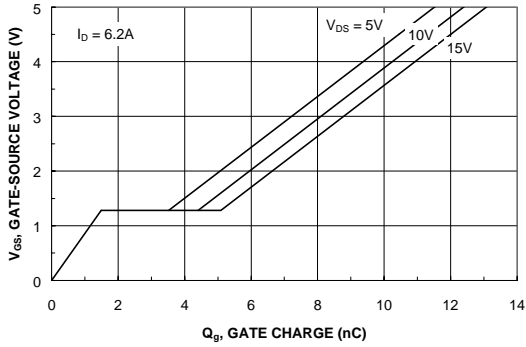
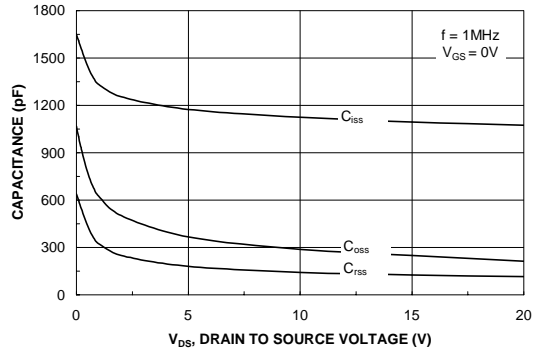


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

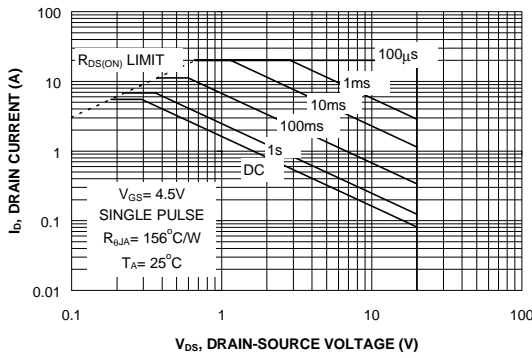
**Typical Characteristics** (continued)



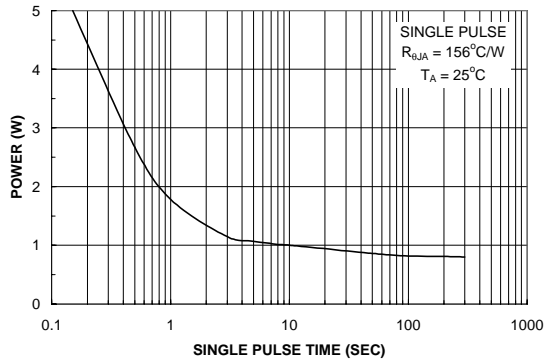
**Figure 7. Gate-Charge Characteristics**



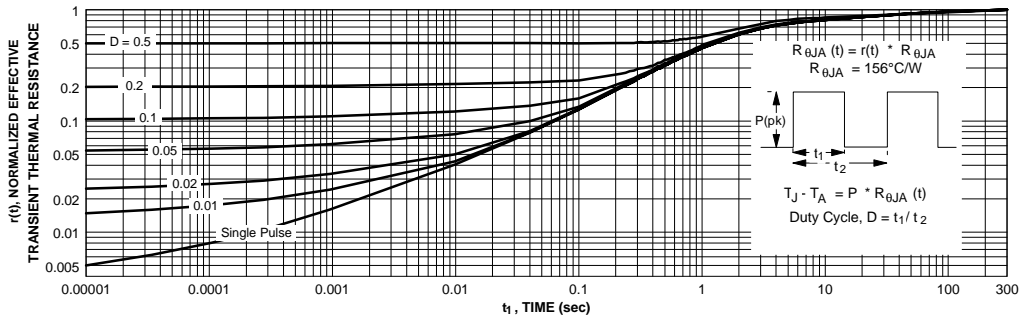
**Figure 8. Capacitance Characteristics**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Single Pulse Maximum Power Dissipation**



**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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